2SC2480

Silicon NPN epitaxial planar type

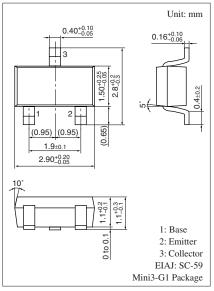
For high-frequency amplification/oscillation/mixing

■ Features

- High transition frequency f_T
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing

■ Absolute Maximum Ratings $T_a = 25$ °C

| Parameter | Symbol | Rating | Unit | |
|---------------------------------------|------------------|-------------|------|--|
| Collector-base voltage (Emitter open) | V _{CBO} | 30 | V | |
| Collector-emitter voltage (Base open) | V _{CEO} | 20 | V | |
| Emitter-base voltage (Collector open) | V_{EBO} | 3 | V | |
| Collector current | I_C | 50 | mA | |
| Collector power dissipation | P _C | 150 | mW | |
| Junction temperature | T_{j} | 150 | °C | |
| Storage temperature | T_{stg} | -55 to +150 | °C | |



Marking Symbol: R

\blacksquare Electrical Characteristics $T_a = 25 ^{\circ}C \pm 3 ^{\circ}C$

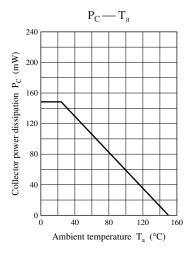
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--------------------------------------------------|------------------|--------------------------------------------------------------------|-----|------|------|------|
| Collector-base voltage (Emitter open) | V _{CBO} | $I_C = 100 \ \mu A, I_E = 0$ | 30 | | | V |
| Emitter-base voltage (Collector open) | V_{EBO} | $I_E = 10 \ \mu A, I_C = 0$ | 3 | | | V |
| Base-emitter voltage | V_{BE} | $V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}$ | | 720 | | mV |
| Forward current transfer ratio * | h_{FE} | $V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}$ | 25 | | 250 | _ |
| Transition frequency | f_T | $V_{CB} = 10 \text{ V}, I_E = -15 \text{ mA}, f = 200 \text{ MHz}$ | 800 | 1300 | 1600 | MHz |
| Reverse transfer capacitance (Common base) | C _{rb} | $V_{CE} = 6 \text{ V}, I_{C} = 0, f = 1 \text{ MHz}$ | | 0.8 | | pF |
| Reverse transfer capacitance (Common emitter) | C _{re} | $V_{CB} = 10 \text{ V}, I_E = -1 \text{ mA}, f = 10.7 \text{ MHz}$ | | 1.0 | 1.5 | pF |
| Power gain | G_{P} | $V_{CB} = 10 \text{ V}, I_E = -1 \text{ mA}, f = 200 \text{ MHz}$ | | 20 | | dB |

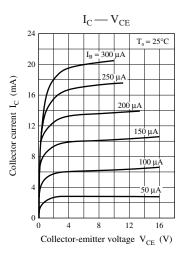
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

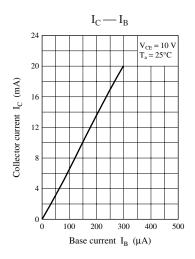
2. *: Rank classification

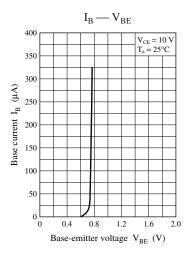
| Rank | Т | S | No-rank | | |
|-------------------|-------------|--------------|-------------|--|--|
| h_{FE} | 800 to 1400 | 1000 to 1600 | 800 to 1600 | | |
| Marking symbol | RT | RS | R | | |

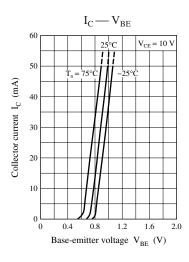
Product of no-rank is not classified and have no indication for rank.

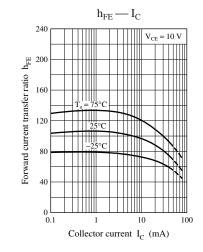


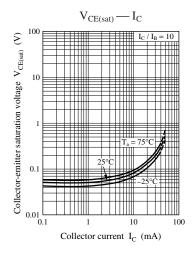


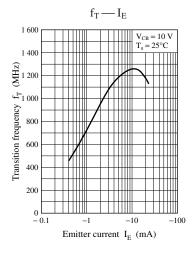


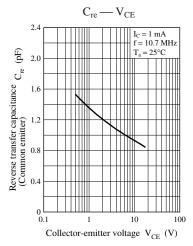


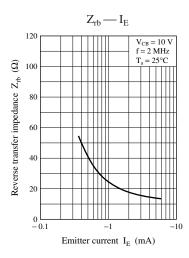


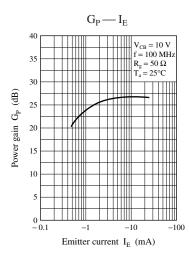


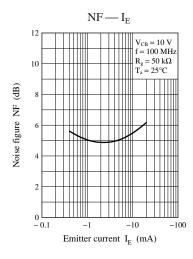


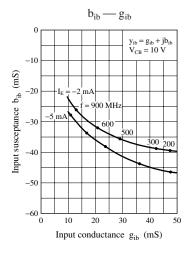


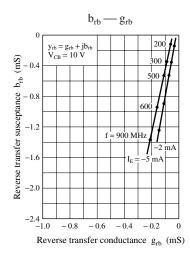


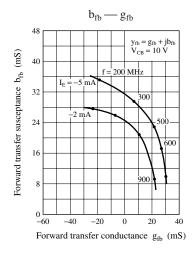


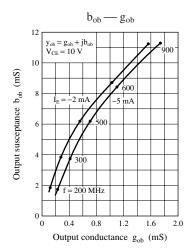












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